# Rectifier - STEALTH™ II 8 A, 600 V

## FFD08S60S-F085

The FFD08S60S–F085 is stealth 2 rectifier with soft recovery characteristics ( $t_{rr}$  < 30 ns). They has half the recovery time of hyperfast rectifier and are silicon nitride passivated ion–implanted epitaxial planar construction. This device is intended for use as freewheeling of boost diode in switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

#### **Features**

- High Speed Switching (Max.  $t_{rr} < 30$  ns @  $I_F = 8$  A)
- High Reverse Voltage and High Reliability
- Avalanche Energy Rated
- AEC-Q101 Qualified and PPAP Capable
- Pb-Free and RoHS Compliant

## **Applications**

- General Purpose
- Switching Mode Power Supply
- Boost Diode in Continuous Mode Power Factor Corrections
- Power Switching Circuits

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage	600	V
V <sub>RWM</sub>	Working Peak Reverse Voltage	600	V
V <sub>R</sub>	DC Blocking Voltage	600	V
I <sub>F(AV)</sub>	Average Rectified Forward Current @ T <sub>C</sub> = 115°C	8	Α
I <sub>FSM</sub>	Non-repetitive Peak Surge Current 60 Hz Single Half-Sine Wave	80	Α
$T_J, T_{STG}$	Operating Junction and Storage Temperature	-65 to + 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

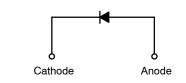
Symbol	Parameter	Ratings	Unit
$R_{ heta JC}$	Maximum Thermal Resistance, Junction to Case	3.0	°C/W

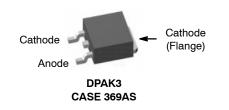
1



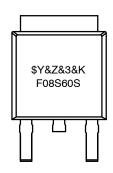
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#### **MARKING DIAGRAM**



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code &3 = Numeric Date Code &K = Lot Code F08S60S = Specific Device Code

## **ORDERING INFORMATION**

Device	Package	Shipping		
FFD08S60-F085	DPAK3 (Pb-Free)	2500 / Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

### FFD08S60S-F085

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V <sub>FM</sub> (Note 1)	I <sub>F</sub> = 8 A, I <sub>F</sub> = 8 A	T <sub>C</sub> = 25°C T <sub>C</sub> = 125°C	- -	2.1 1.6	2.6 -	V
I <sub>RM</sub> (Note 1)	V <sub>R</sub> = 600 V, V <sub>R</sub> = 600 V	T <sub>C</sub> = 25°C T <sub>C</sub> = 125°C	- -	- -	100 500	μΑ
t <sub>rr</sub>	$I_F = 1 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s, V}_R = 30 \text{ V}$	T <sub>C</sub> = 25°C	-	_	25	ns
t <sub>rr</sub>	I <sub>F</sub> = 8 A, di/dt = 200 A/μs, V <sub>R</sub> = 390 V	T <sub>C</sub> = 25°C	_	19	30	ns
I <sub>rr</sub>			_	2.2	-	Α
S factor			_	0.6	_	
Q <sub>rr</sub>			_	21	_	nC
t <sub>rr</sub>	$I_F = 8 \text{ A, di/dt} = 200 \text{ A/}\mu\text{s, V}_R = 390 \text{ V}$	T <sub>C</sub> = 125°C	-	58	-	ns
I <sub>rr</sub>			_	4.3	-	Α
S factor			_	1.3	-	
Q <sub>rr</sub>				125		nC
$W_{AVL}$	Avalanche Energy (L = 40 mH)		20	_	_	mJ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### **TEST CIRCUIT AND WAVEFORMS**

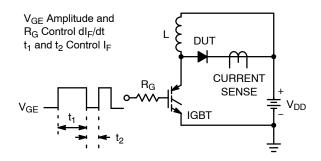


Figure 1. t<sub>rr</sub> Test Circuit

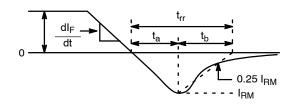


Figure 2. t<sub>rr</sub> Waveform and Definitions

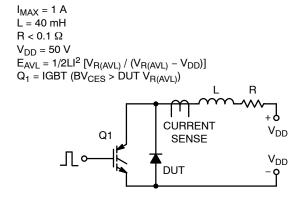


Figure 3. Avalanche Energy Test Circuit

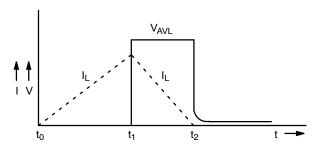


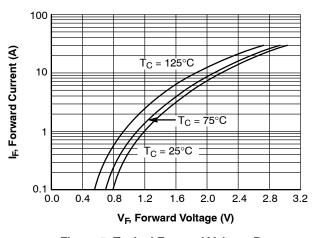
Figure 4. Avalanche Current and Voltage Waveforms

<sup>1.</sup> Pulse: Test Pulse width = 300 μs, Duty Cycle = 2%.

## FFD08S60S-F085

### **TYPICAL CHARACTERISTICS**

(T<sub>C</sub> = 25°C unless otherwise noted)



1E-4

1E-5

1E-6

T<sub>C</sub> = 125°C

1E-7

1E-7

1E-8

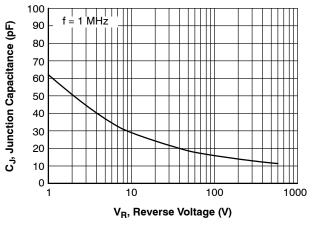
1E-9

0 100 200 300 400 500 600

V<sub>R</sub>, Reverse Voltage (V)

Figure 5. Typical Forward Voltage Drop

**Figure 6. Typical Reverse Current** 



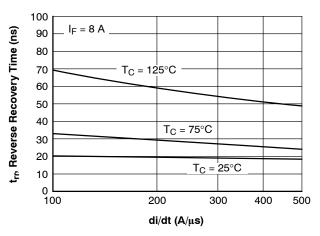
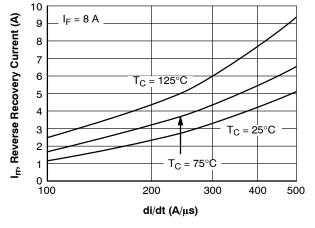


Figure 7. Typical Junction Capacitance

Figure 8. Typical Reverse Recovery Time



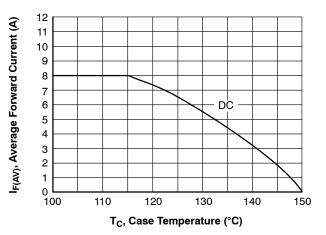
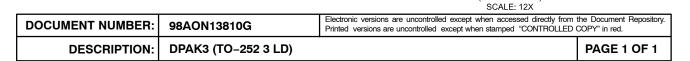


Figure 9. Typical Reverse Recovery Current

Figure 10. Forward Current Deration Curve

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### DPAK3 (TO-252 3 LD) CASE 369AS **ISSUE O DATE 30 SEP 2016** 6.73 6.35 5,46 5.55 MIN-6.50 MIN 6.40 Ċ 0.25 MAX PLASTIC BODY STUB MIN DIODE PRODUCTS VERSION (0.59)-1.25 MIN 0.89 ⊕ 0.25 M AM C 2.29 2.28 4.56 4.57 LAND PATTERN RECOMMENDATION NON-DIODE PRODUCTS VERSION В 2.39 SEE 2.18 4.32 MIN NOTE D 0.58 0.45 5.21 MIN 10.41 9.40 SEE DETAIL A 2 3 NON-DIODE PRODUCTS VERSION DIODE PRODUCTS VERSION ○ 0.10 B 0,51 **GAGE PLANE** NOTES: UNLESS OTHERWISE SPECIFIED 0.61 0.45 A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, (1.54)ISSUE C, VARIATION AA. B) ALL DIMENSIONS ARE IN MILLIMETERS. C) DIMENSIONING AND TOLERANCING PER 10° ASME Y14.5M-2009. D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED 1 78 CORNERS OR EDGE PROTRUSION.



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G) LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.

F) DIMENSIONS ARE EXCLUSSIVE OF BURSS,

MOLD FLASH AND TIE BAR EXTRUSIONS.

0.127 MAX

**DETAIL A** (ROTATED -90°)

**SEATING PLANE** 

1,40

(2.90)

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